

In the Specification:

On page 6, amend the paragraph beginning on line 24 as follows:

Another aspect of the invention is directed to a method for fabricating an optically pumped semiconductor device having a semiconductor body which includes a surface-emitting quantum well structure and at least one pump radiation source which generates pump radiation for optically pumping the quantum well structure, the pump radiation source and the quantum well structure being monolithically integrated. A substrate is provided, and a plurality of semiconductor layers are epitaxially grown on the substrate, which layers include the pump radiation source ~~and form the quantum well structure~~. A window is formed in the plurality of semiconductor layers for the quantum well structure, and the quantum well structure is epitaxially grown in the window so that the pump radiation source adjoins the quantum well structure. A recess for introducing the pump radiation into the quantum well structure is formed between the pump radiation source and the quantum well structure.